AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the present application.

Listing of Claims:

Claim 1 (currently amended): For semiconductor manufacturing equipment, a ceramic susceptor comprising:

a ceramic substrate defining a wafer-support side; and

a resistive heating element composed of wiring lines formed from a conductive paste print-coated in a predetermined configuration on either a surface of or inside said ceramic substrate, the conductive paste of viscosity selected so that as print-coated, the wiring lines ~~being~~ take on a substantially trapezoidal form in cross-section, ~~the wiring lines further~~ defining bottom and inclined lateral sides, ~~in a predetermined configuration provided on either a surface of or inside said ceramic substrate, said resistive heating element being configured~~ and so that in section through said wiring lines the smallest angle formed by the bottom and the lateral sides is 5° or greater.

Claim 2 (previously presented): A ceramic susceptor as set forth in claim 1, wherein when a wafer is placed on the wafer support side and said resistive heating element is drawing current, heated deviation in the wafer surface temperature is ±1.0% or less at working temperature.

Claim 3 (previously presented): A ceramic susceptor as set forth in claim 2, wherein deviation in the wafer surface temperature is within ± 0.5% at working temperature.

Claim 4 (previously presented): A ceramic susceptor as set forth in claim 1, wherein said ceramic substrate is made of at least one ceramic selected from aluminum nitride, silicon nitride, aluminum oxynitride, and silicon carbide.

Claim 5 (previously presented): A ceramic susceptor as set forth in claim 1, wherein said ceramic substrate is either aluminum nitride or silicon carbide of 100 W/m·K or greater thermal conductivity.

Claim 6 (previously presented): A ceramic susceptor as set forth in claim 1, wherein said resistive heating element is made from at least one medal selected from tungsten, molybdenum, platinum, palladium, silver, nickel, and chrome.

Claim 7 (previously presented): A ceramic susceptor as set forth in claim 1, further comprising a plasma electrode disposed either on a surface of or inside said ceramic substrate.

Claim 8 (previously presented): A ceramic susceptor as set forth in claim 2, wherein said ceramic substrate is made of at least one ceramic selected from aluminum nitride, silicon nitride, aluminum oxynitride, and silicon carbide.

Claim 9 (previously presented): A ceramic susceptor as set forth in claim 3, wherein said ceramic substrate is made of at least one ceramic selected from aluminum nitride, silicon nitride, aluminum oxynitride, and silicon carbide.

Claim 10 (previously presented): A ceramic susceptor as set forth in claim 9, wherein said ceramic substrate is either aluminum nitride or silicon carbide of 100 W/m·K or greater thermal conductivity.

Claim 11 (previously presented): A ceramic susceptor as set forth in claim 10, wherein said resistive heating element is made from at least one medal selected from tungsten, molybdenum, platinum, palladium, silver, nickel, and chrome.

Claim 12 (previously presented): A ceramic susceptor as set forth in claim 2, further comprising a plasma electrode disposed either on a surface of or inside said ceramic substrate.

Claim 13 (previously presented): A ceramic susceptor as set forth in claim 4, further comprising a plasma electrode disposed either on a surface of or inside said ceramic substrate.

Claim 14 (previously presented): A ceramic susceptor as set forth in claim 11, further comprising a plasma electrode disposed either on a surface of or inside said ceramic substrate.